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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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LOW POWER PNP TRANSISTOR

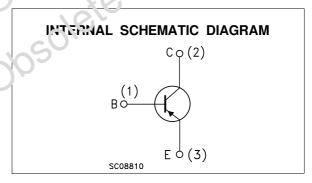
Ordering Code	Marking		
BCP52-16	BCP5216		

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BCP55-16

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





AESOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	V
VOEO	Collector-Emitter Voltage (I _B = 0)	-60	V
/C∈R	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-60	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V
Ic	Collector Current	-1	Α
I _{CM}	Collector Peak Current (t _p < 5 ms)	-1.5	Α
lΒ	Base Current	-0.1	Α
I _{BM}	Base Peak Current (t _p < 5 ms)	-0.2	Α
P _{tot}	Total Dissipation at T _{amb} = 25 °C	1.4	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

September 2003 1/4

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	89.3	°C/W	
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Device mounted on a PCB area of 1 cm²

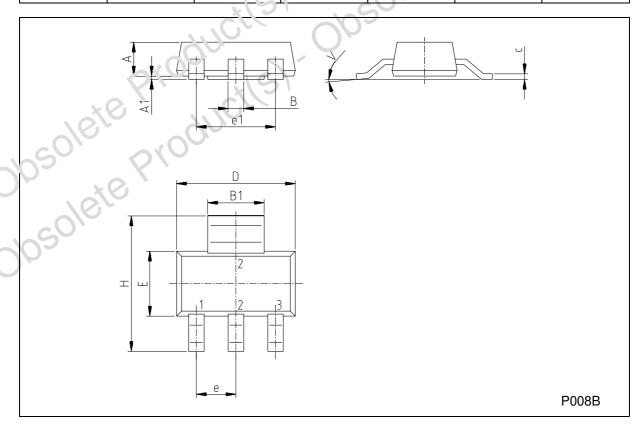
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = -30 \text{ V}$ $V_{CB} = -30 \text{ V}$ $T_j = 125 ^{\circ}\text{C}$			-100 -10	nA μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA	-60		Cil	5 Y
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage (R _{BE} = 1 KΩ)	$I_C = -100 \mu A$	-60	OQ/)* 	V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	5	Al	Cir	V
$V_{\text{CE}(\text{sat})^{*}}$	Collector-Emitter Saturation Voltage	$I_C = -500 \text{ mA}$ $I_B = -50 \text{ mA}$	01	00	-0.5	V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = -500 mA V _{CL} 2 V	6		-1	V
h _{FE} *	DC Current Gain	Ic = -5 mA	40 100 25		250	
f _T	Transition Frequency	$I_C = -10 \text{ mA } V_{CE} = -5 \text{ V} \text{ f} = 20 \text{ M}$	Ηz	50		MHz
0501	Transition Frequency e duration = 300 μs, dut, ο, ο, ο s	cils				

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SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			1.80			0.071
В	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
С	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
е		2.30			C 0è 0	16
e1		4.60		v.O.	0.181	cilla
E	3.30	3.50	3.70	(120	0.138	0.146
Н	6.70	7.00	7.30	0.264	0.276	0.287
V			10°	3%		10°
A1		0.02		Vier		



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